

TRENCHSTOP™ Series

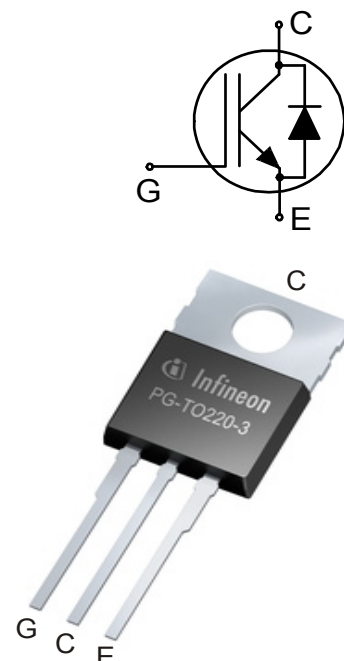
Low Loss DuoPack: IGBT in TRENCHSTOP™ and Fieldstop technology with soft, fast recovery anti-parallel Emitter Controlled diode

Features:

- Automotive AEC Q101 qualified
- Designed for DC/AC converters for Automotive Application
- Very low $V_{CE(sat)}$ 1.5V (typ.)
- Maximum Junction Temperature 150°C
- Dynamically stress tested
- Short circuit withstand time 5μs
- Positive temperature coefficient in $V_{CE(sat)}$
- Low EMI
- Low Gate Charge
- Green Package
- TRENCHSTOP™ and Fieldstop technology for 600V applications offers:
 - very tight parameter distribution
 - high ruggedness, temperature stable behavior
 - very high switching speed

Applications:

- Main inverter
- Climate compressor
- PTC heater
- Motor drives

**Key Performance and Package Parameters**

Type	V_{CE}	I_C	V_{CEsat} , $T_{vj}=25^{\circ}C$	T_{vjmax}	Marking	Package
AIKP20N60CT	600V	20A	1.5V	150°C	AK20DCT	PG-TO220-3



TRENCHSTOP™ Series

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TRENCHSTOP™ Series

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{CE}	600	V
DC collector current, limited by T_{vjmax} $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_C	40.0 20.0	A
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpuls}	60.0	A
Turn off safe operating area $V_{CE} \leq 600\text{V}$, $T_{vj} \leq 150^{\circ}\text{C}^{1)}$	-	60.0	A
Diode forward current, limited by T_{vjmax} $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_F	40.0 20.0	A
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpuls}	60.0	A
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time $V_{GE} = 15.0\text{V}$, $V_{CC} \leq 400\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 150^{\circ}\text{C}$	t_{SC}	5	μs
Power dissipation $T_C = 25^{\circ}\text{C}$	P_{tot}	156.0	W
Operating junction temperature	T_{vj}	$-40 \dots +150$	$^{\circ}\text{C}$
Storage temperature	T_{stg}	$-40 \dots +150$	$^{\circ}\text{C}$
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	$^{\circ}\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

Thermal Resistance

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R _{th} Characteristics						
IGBT thermal resistance, junction - case	R _{th(j-c)}		-	-	0.90	K/W
Diode thermal resistance, junction - case	R _{th(j-c)}		-	-	1.50	K/W
Thermal resistance junction - ambient	R _{th(j-a)}		-	-	62	K/W

¹⁾ $t_p \leq 1\mu\text{s}$

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Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0V, I_C = 0.20mA$	600	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE} = 15.0V, I_C = 20.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 150^{\circ}C$	- -	1.50 1.85	2.05 -	V
Diode forward voltage	V_F	$V_{GE} = 0V, I_F = 20.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 150^{\circ}C$	- -	1.65 1.65	2.05 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.29mA, V_{CE} = V_{GE}$	4.1	4.9	5.7	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 600V, V_{GE} = 0V$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 150^{\circ}C$	- -	- 550	40 -	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20V, I_C = 20.0A$	-	11.0	-	S
Integrated gate resistor	r_G			none		Ω

Electrical Characteristic, at $T_{vj} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C _{ies}	V _{CE} = 25V, V _{GE} = 0V, f = 1MHz	-	1100	-	pF
Output capacitance	C _{oes}		-	71	-	
Reverse transfer capacitance	C _{res}		-	32	-	
Gate charge	Q _G	V _{CC} = 480V, I _C = 20.0A, V _{GE} = 15V	-	120.0	-	nC
Short circuit collector current Max. 1000 short circuits Time between short circuits: ≥ 1.0s	I _{C(SC)}	V _{GE} = 15.0V, V _{CC} ≤ 400V, t _{SC} ≤ 5μs T _{vj} = 150°C	-	183	-	A

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(\text{on})}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 20.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(\text{on})} = 12.0\Omega, R_{G(\text{off})} = 12.0\Omega,$ $L\sigma = 131\text{nH}, C\sigma = 31\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include “tail” and diode reverse recovery.	-	18	-	ns
Rise time	t_r		-	14	-	ns
Turn-off delay time	$t_{d(\text{off})}$		-	199	-	ns
Fall time	t_f		-	42	-	ns
Turn-on energy	E_{on}		-	0.31	-	mJ
Turn-off energy	E_{off}		-	0.46	-	mJ
Total switching energy	E_{ts}		-	0.77	-	mJ

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Diode Characteristic, at $T_{vj} = 25^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 25^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 20.0\text{A},$ $di_F/dt = 880\text{A}/\mu\text{s}$	-	41	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.31	-	μC
Diode peak reverse recovery current	I_{rrm}		-	13.3	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	711	-	$\text{A}/\mu\text{s}$

Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

IGBT Characteristic, at $T_{vj} = 150^{\circ}\text{C}$

Turn-on delay time	$t_{d(on)}$	$T_{vj} = 150^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 20.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(on)} = 12.0\Omega, R_{G(off)} = 12.0\Omega,$ $L\sigma = 131\text{nH}, C\sigma = 31\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	18	-	ns
Rise time	t_r		-	17	-	ns
Turn-off delay time	$t_{d(off)}$		-	217	-	ns
Fall time	t_f		-	70	-	ns
Turn-on energy	E_{on}		-	0.47	-	mJ
Turn-off energy	E_{off}		-	0.60	-	mJ
Total switching energy	E_{ts}		-	1.07	-	mJ

Diode Characteristic, at $T_{vj} = 150^{\circ}\text{C}$

Diode reverse recovery time	t_{rr}	$T_{vj} = 150^{\circ}\text{C},$ $V_R = 400\text{V},$ $I_F = 20.0\text{A},$ $di_F/dt = 800\text{A}/\mu\text{s}$	-	201	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.28	-	μC
Diode peak reverse recovery current	I_{rrm}		-	16.6	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	481	-	$\text{A}/\mu\text{s}$

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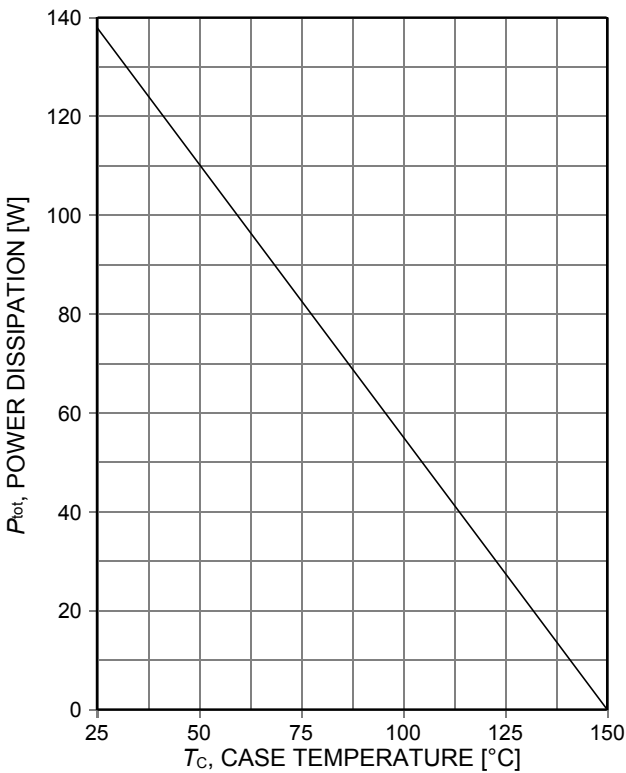


Figure 1. **Power dissipation as a function of case temperature**
($T_J \leq 150^\circ\text{C}$)

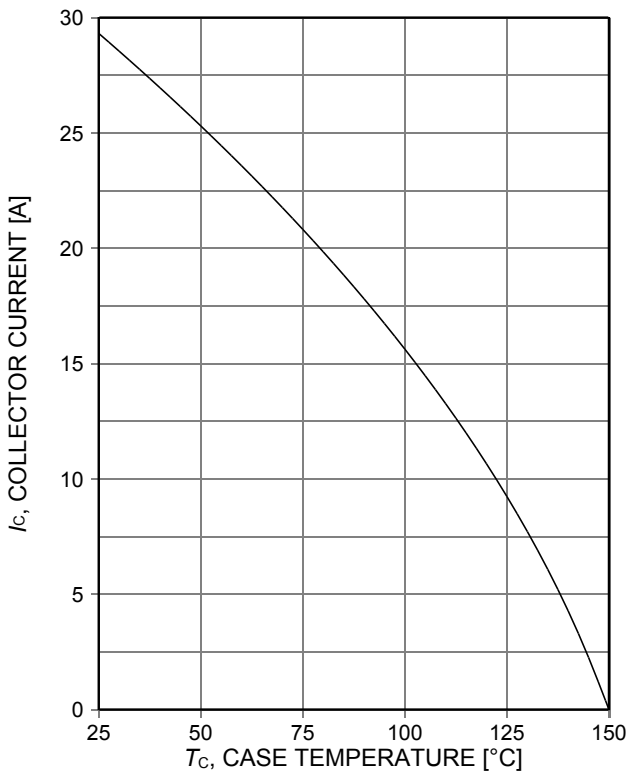


Figure 2. **Collector current as a function of case temperature**
($V_{GE} \geq 15\text{V}$, $T_J \leq 150^\circ\text{C}$)

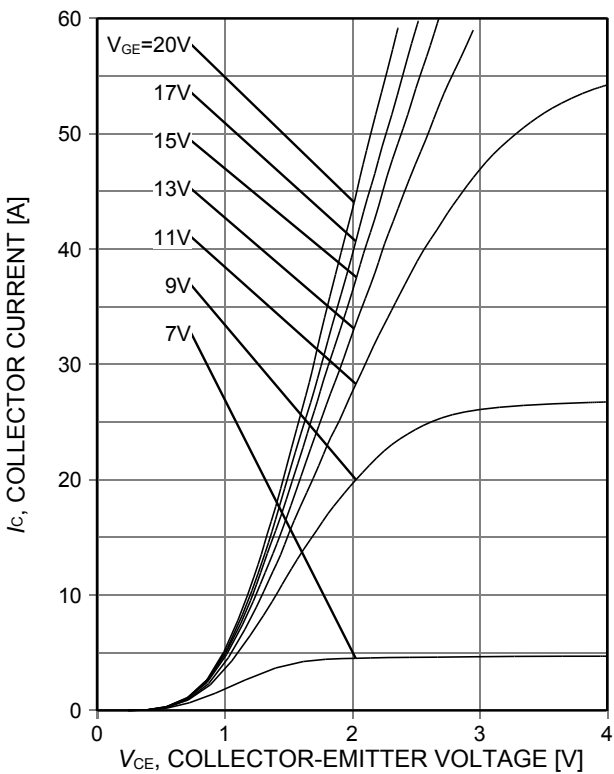


Figure 3. **Typical output characteristic**
($T_J = 25^\circ\text{C}$)

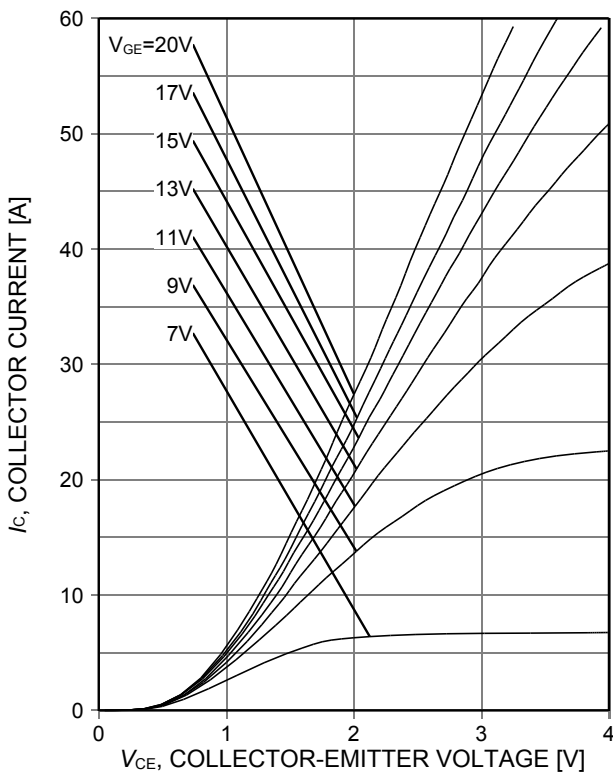


Figure 4. **Typical output characteristic**
($T_J = 150^\circ\text{C}$)

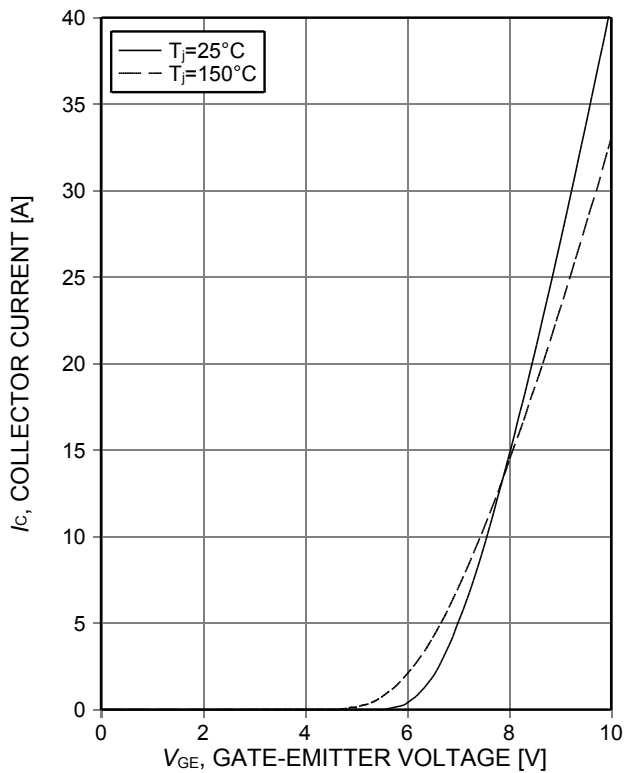


Figure 5. **Typical transfer characteristic**
($V_{CE}=10V$)

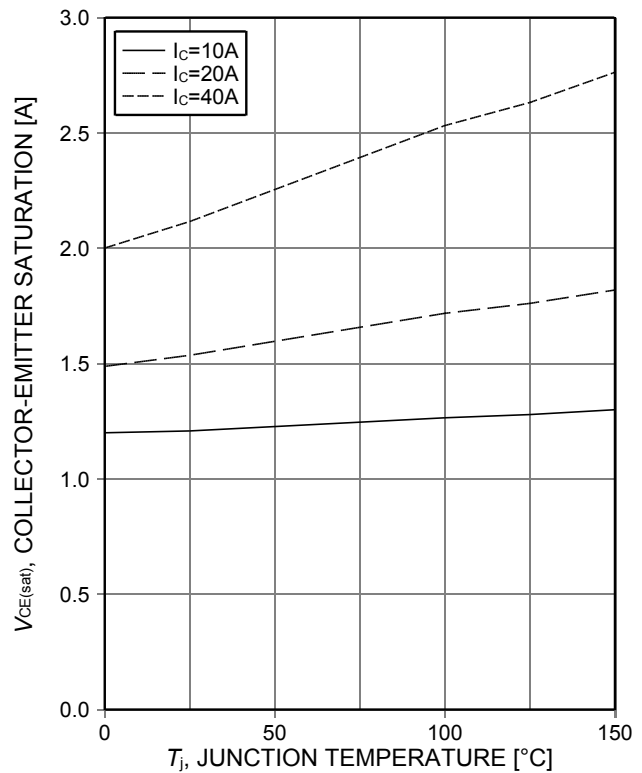


Figure 6. **Typical collector-emitter saturation voltage as a function of junction temperature**
($V_{GE}=15V$)

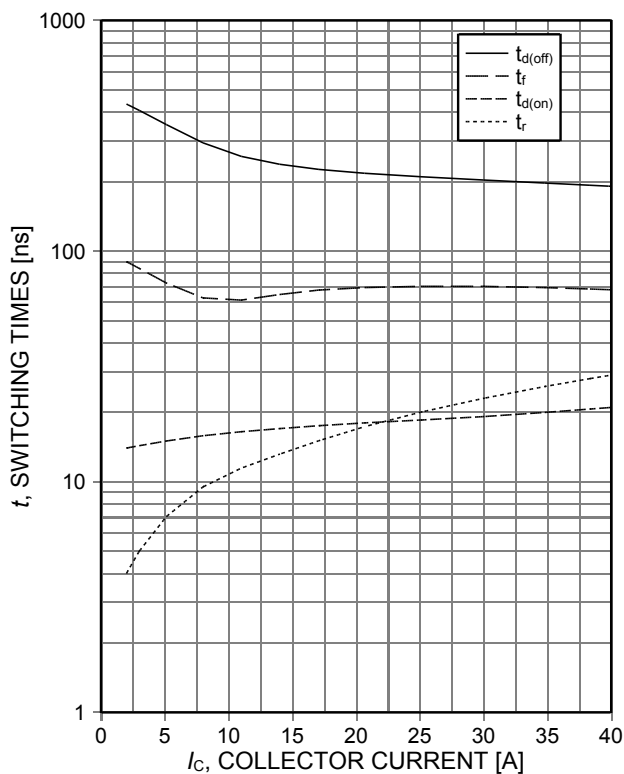


Figure 7. **Typical switching times as a function of collector current**
(inductive load, $T_J=150^\circ C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $R_G=12\Omega$, Dynamic test circuit in Figure E)

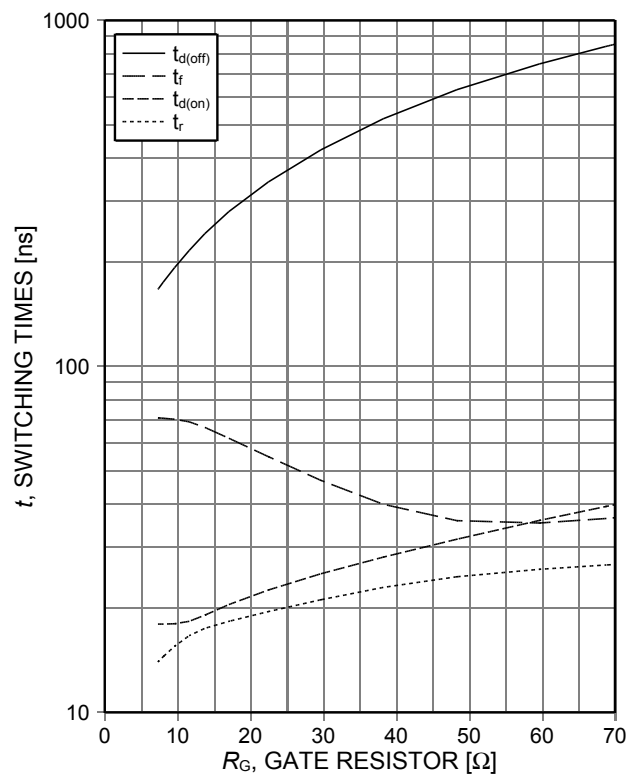


Figure 8. **Typical switching times as a function of gate resistor**
(inductive load, $T_J=150^\circ C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=20A$, Dynamic test circuit in Figure E)

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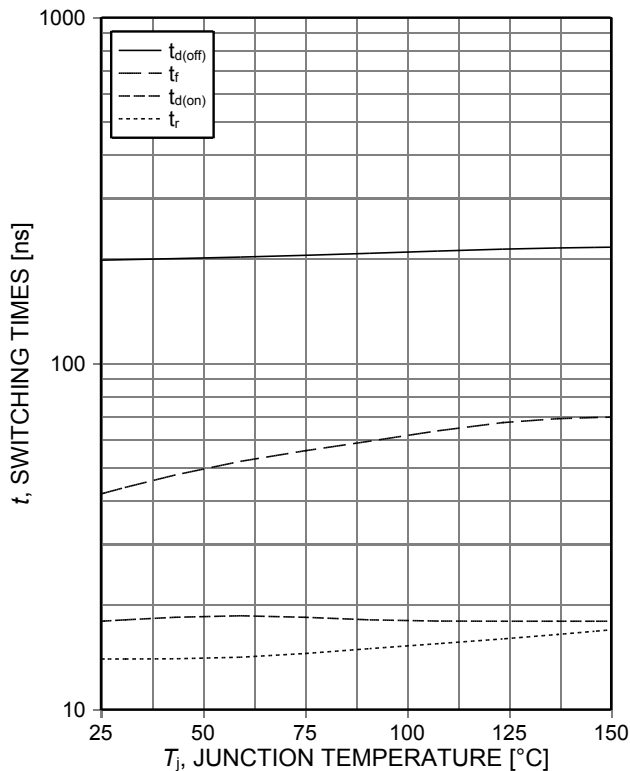


Figure 9. **Typical switching times as a function of junction temperature**
(inductive load, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=20A$, $R_G=12\Omega$, Dynamic test circuit in Figure E)

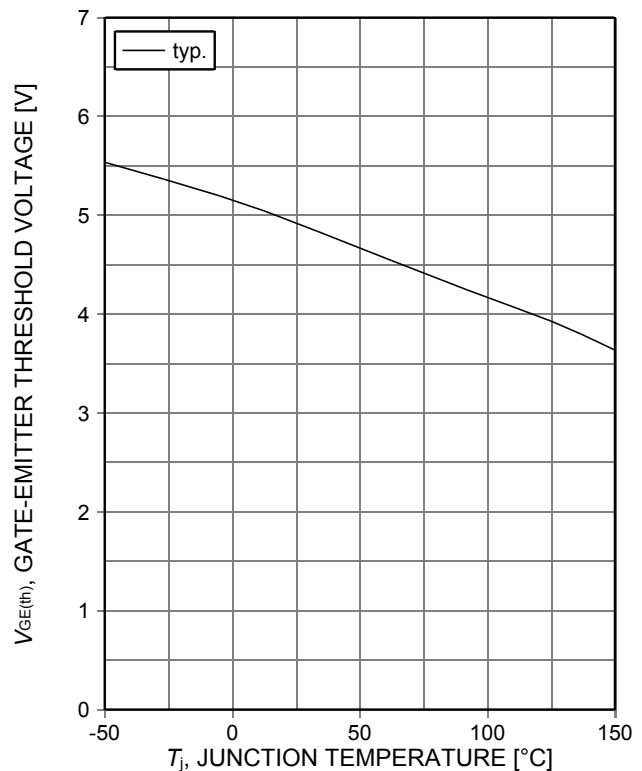


Figure 10. **Gate-emitter threshold voltage as a function of junction temperature**
($I_C=0.29mA$)

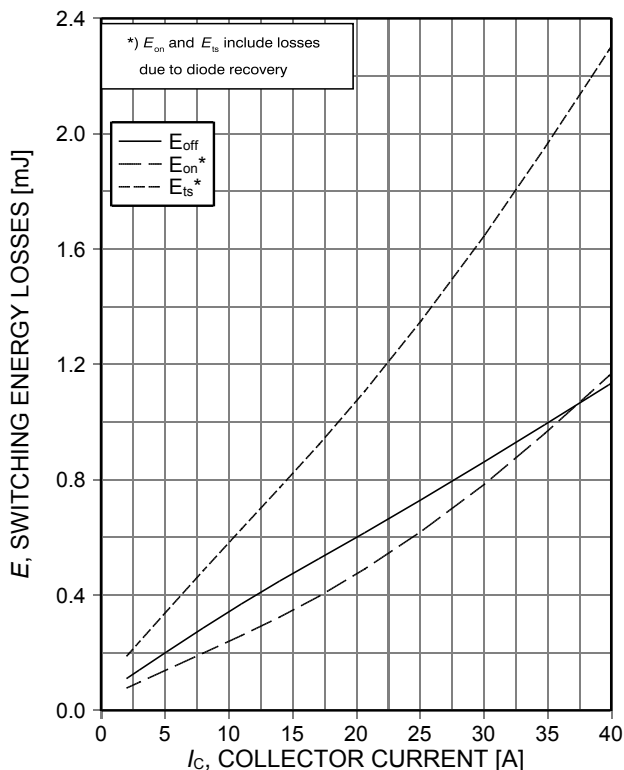


Figure 11. **Typical switching energy losses as a function of collector current**
(inductive load, $T_j=150^\circ C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $R_G=12\Omega$, Dynamic test circuit in Figure E)

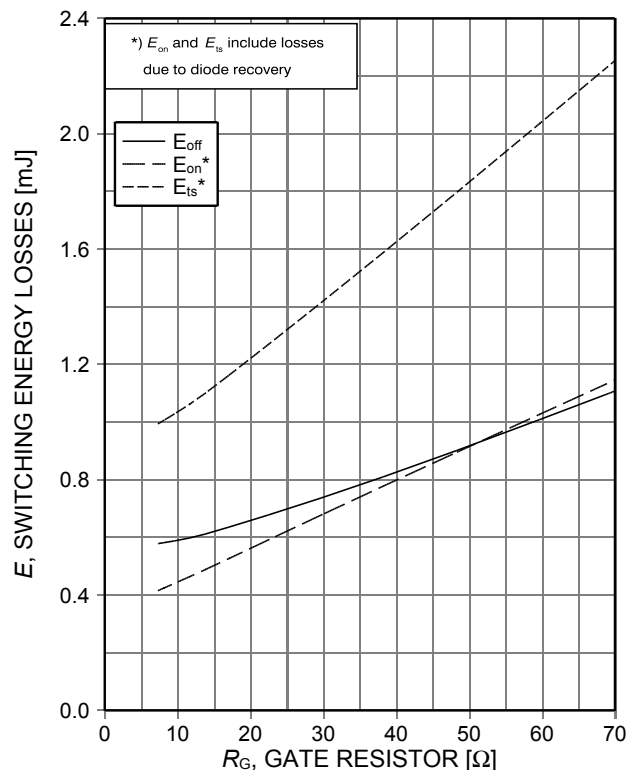


Figure 12. **Typical switching energy losses as a function of gate resistor**
(inductive load, $T_j=150^\circ C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=20A$, Dynamic test circuit in Figure E)

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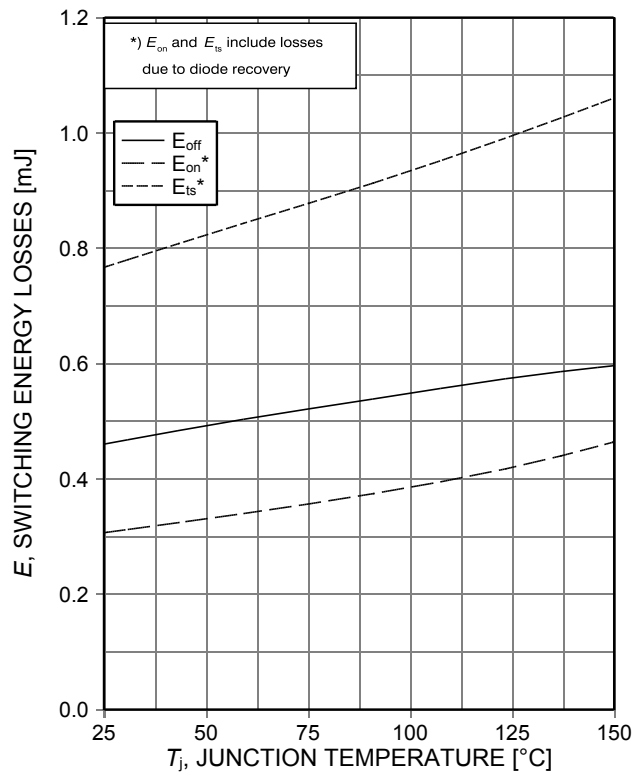


Figure 13. **Typical switching energy losses as a function of junction temperature**
(inductive load, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=20A$, $R_G=12\Omega$, Dynamic test circuit in Figure E)

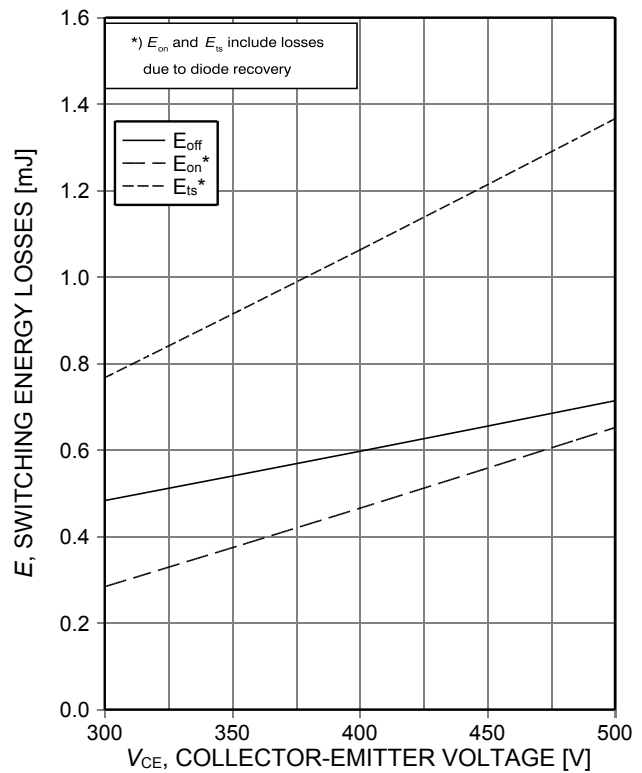


Figure 14. **Typical switching energy losses as a function of collector-emitter voltage**
(inductive load, $T_j=150^\circ C$, $V_{GE}=15/0V$, $I_C=20A$, $R_G=12\Omega$, Dynamic test circuit in Figure E)

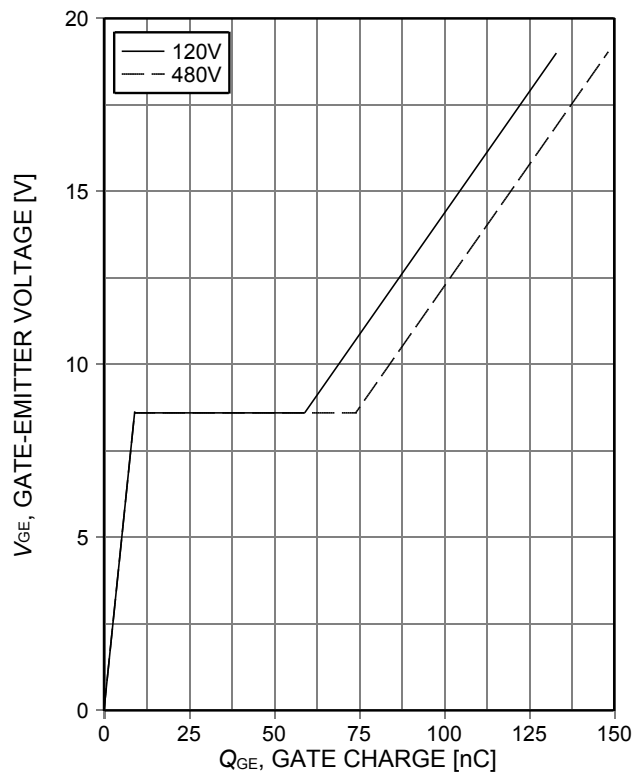


Figure 15. **Typical gate charge**
($I_C=20A$)

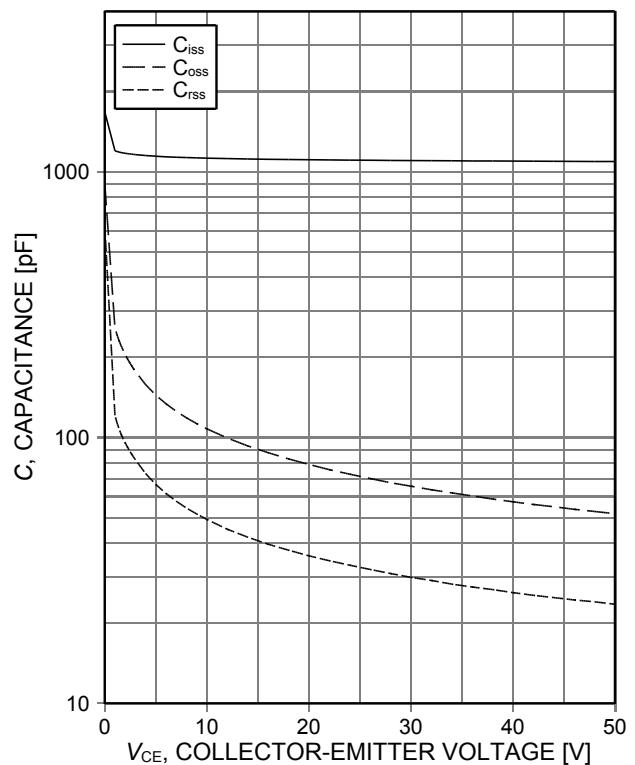


Figure 16. **Typical capacitance as a function of collector-emitter voltage**
($V_{GE}=0V$, $f=1MHz$)

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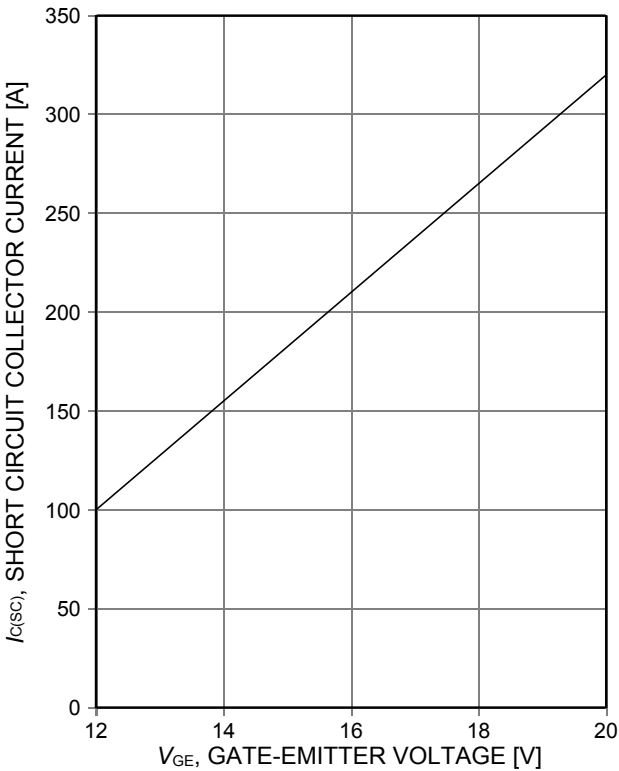


Figure 17. Typical short circuit collector current as a function of gate-emitter voltage ($V_{CE} \leq 400V$, $T_J \leq 150^\circ C$)

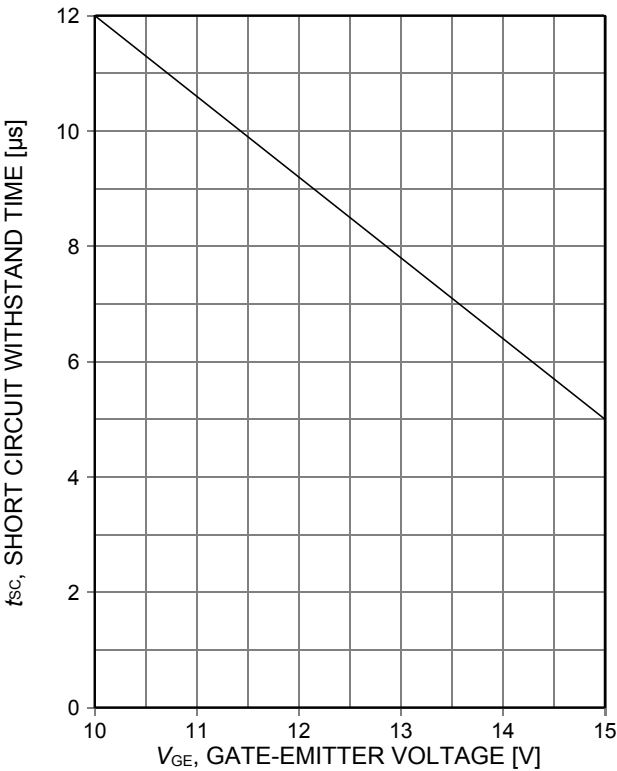


Figure 18. Short circuit withstand time as a function of gate-emitter voltage ($V_{CE} = 400V$, start at $T_J = 25^\circ C$, $T_{Jmax} \leq 150^\circ C$)

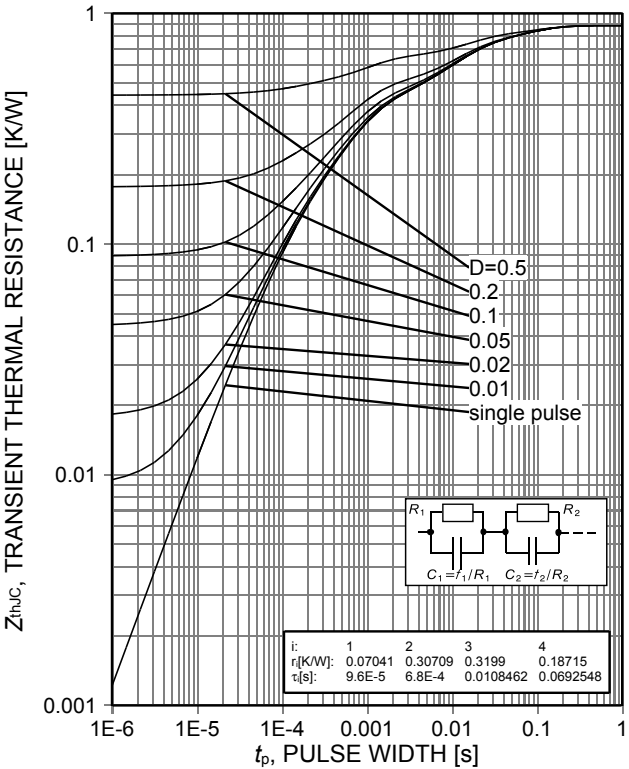


Figure 19. IGBT transient thermal resistance as a function of pulse width for different duty cycles D ($D = t_p/T$)

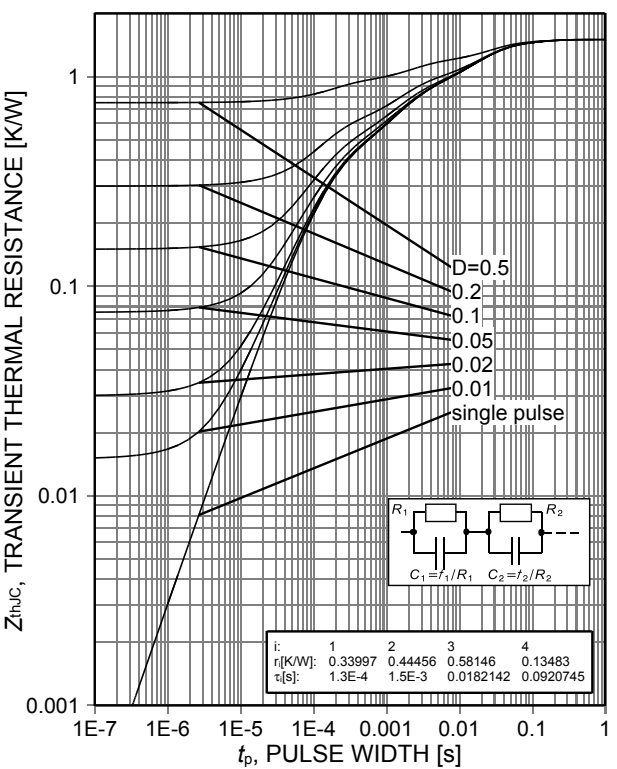


Figure 20. Diode transient thermal impedance as a function of pulse width for different duty cycles D ($D = t_p/T$)

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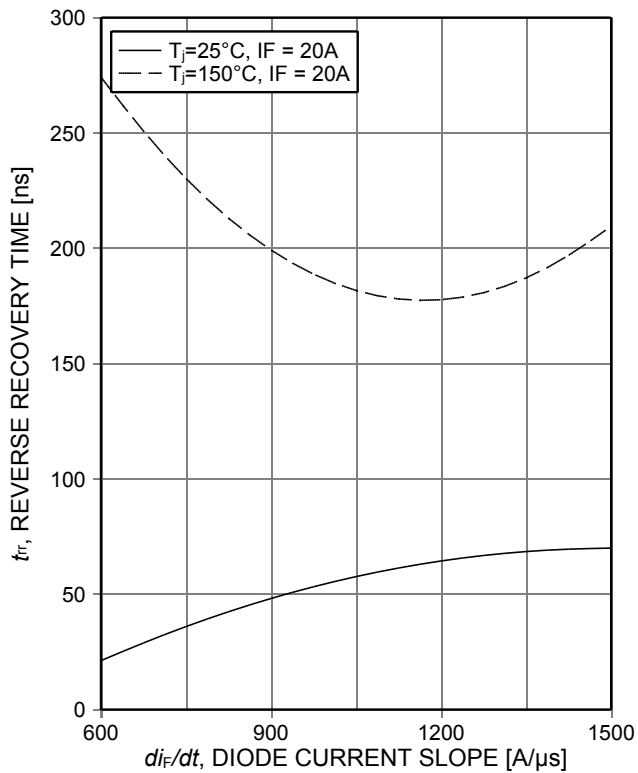


Figure 21. **Typical reverse recovery time as a function of diode current slope**
($V_R=400V$, Dynamic test circuit in Figure E)

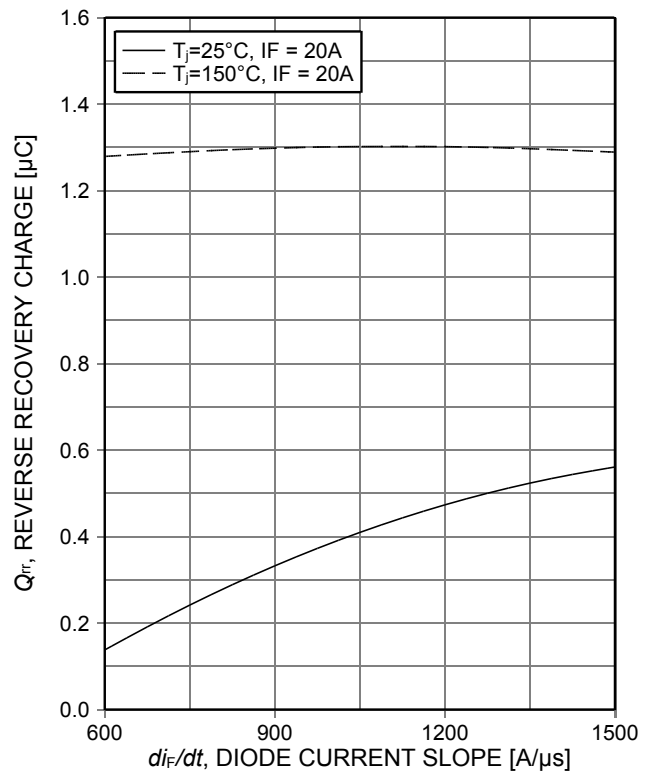


Figure 22. **Typical reverse recovery charge as a function of diode current slope**
($V_R=400V$, Dynamic test circuit in Figure E)

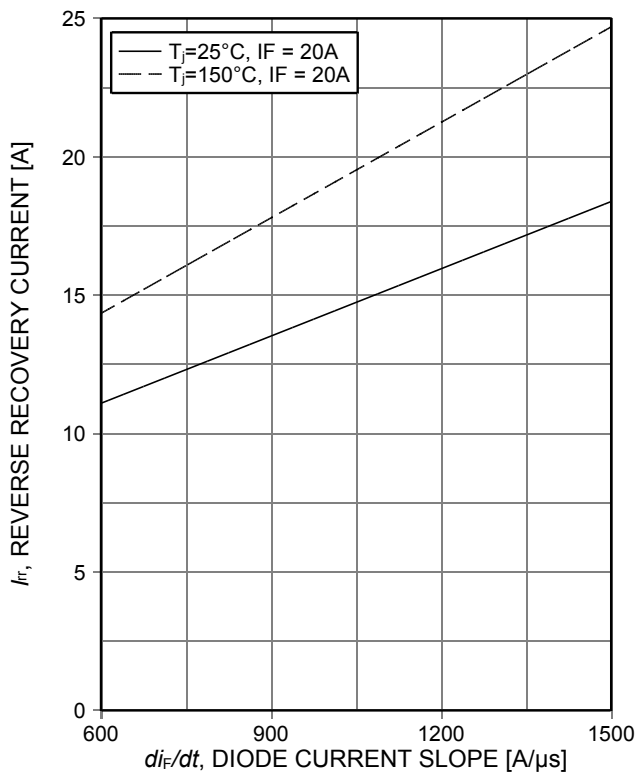


Figure 23. **Typical reverse recovery current as a function of diode current slope**
($V_R=400V$, Dynamic test circuit in Figure E)

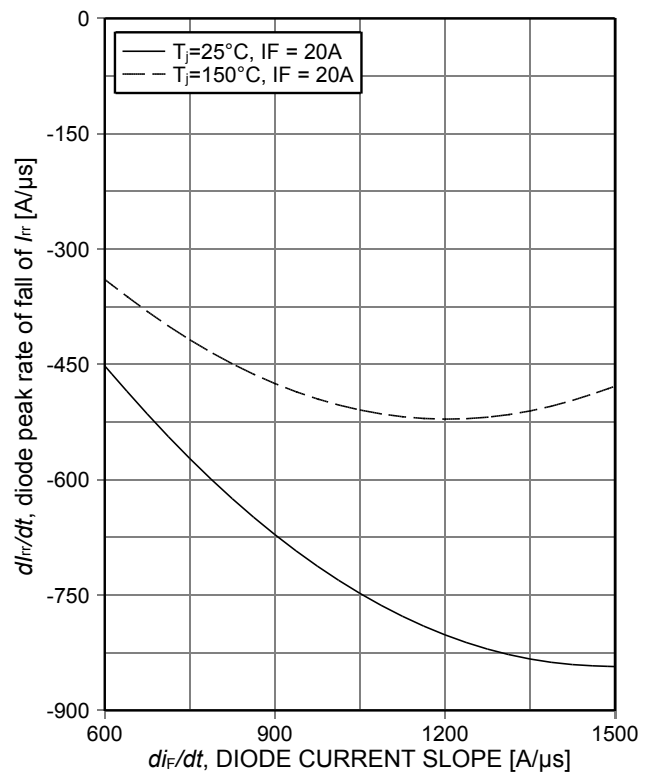


Figure 24. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**
($V_R=400V$, Dynamic test circuit in Figure E)

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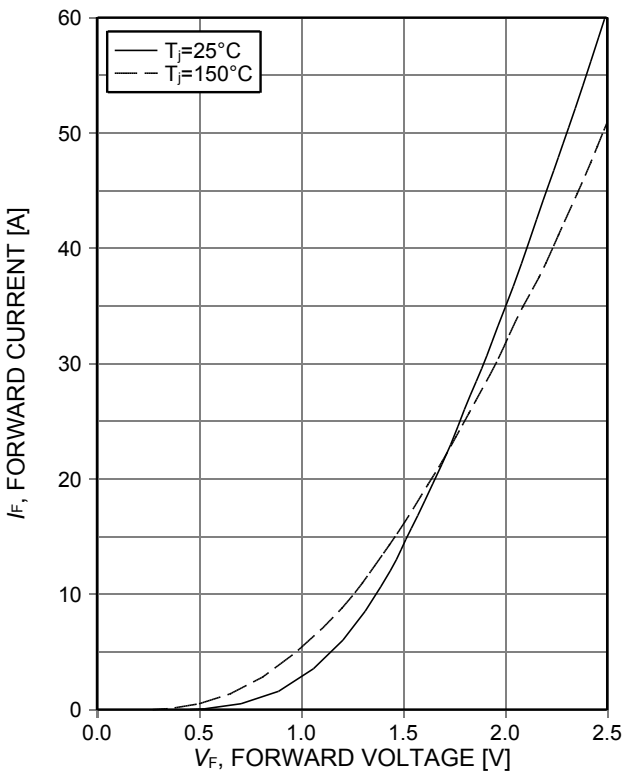


Figure 25. Typical diode forward current as a function of forward voltage

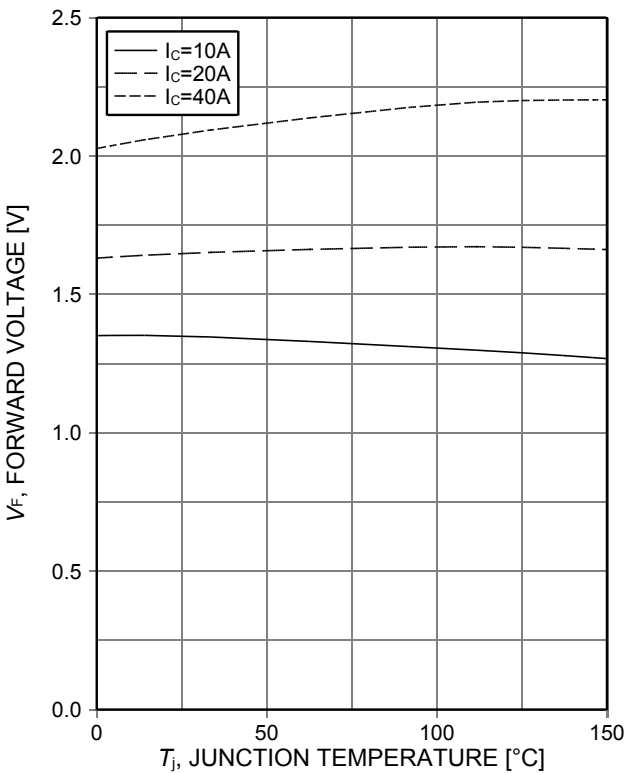
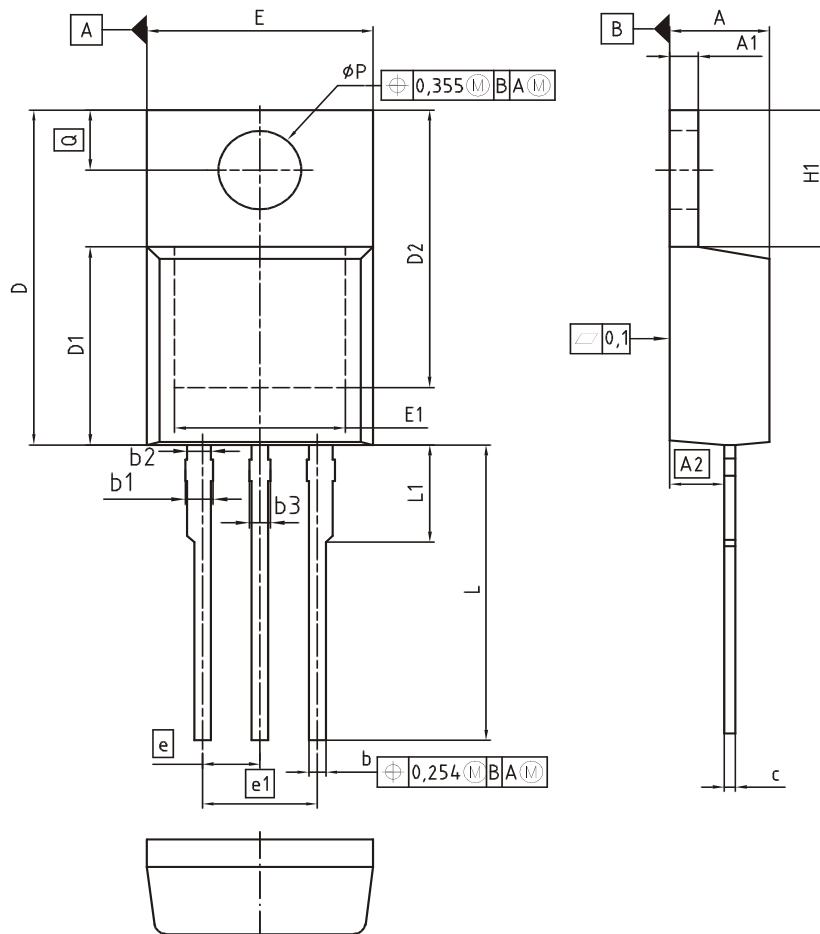
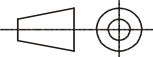


Figure 26. Typical diode forward voltage as a function of junction temperature

Package Drawing PG-TO220-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
ϕP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

DOCUMENT NO. Z8B00003318
SCALE 0 2.5 5mm
EUROPEAN PROJECTION 
ISSUE DATE 30-07-2009
REVISION 06

Testing Conditions

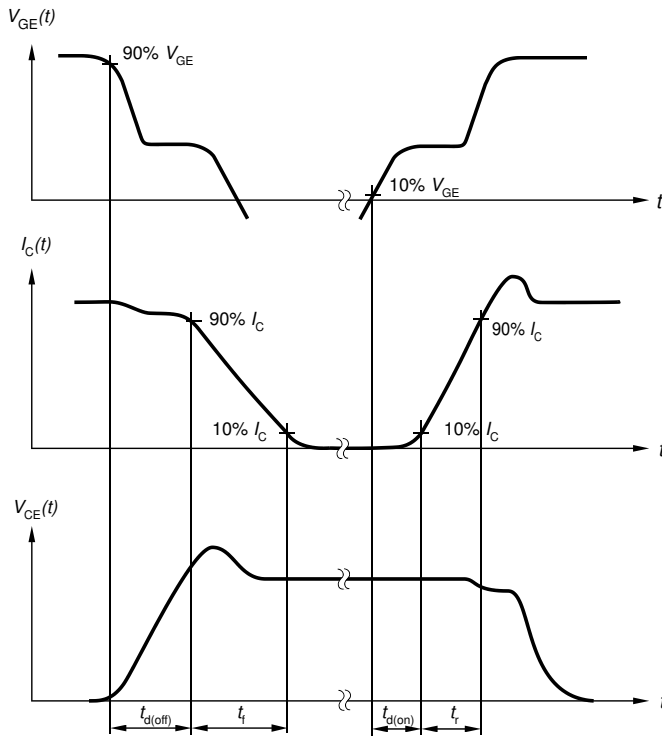


Figure A. Definition of switching times

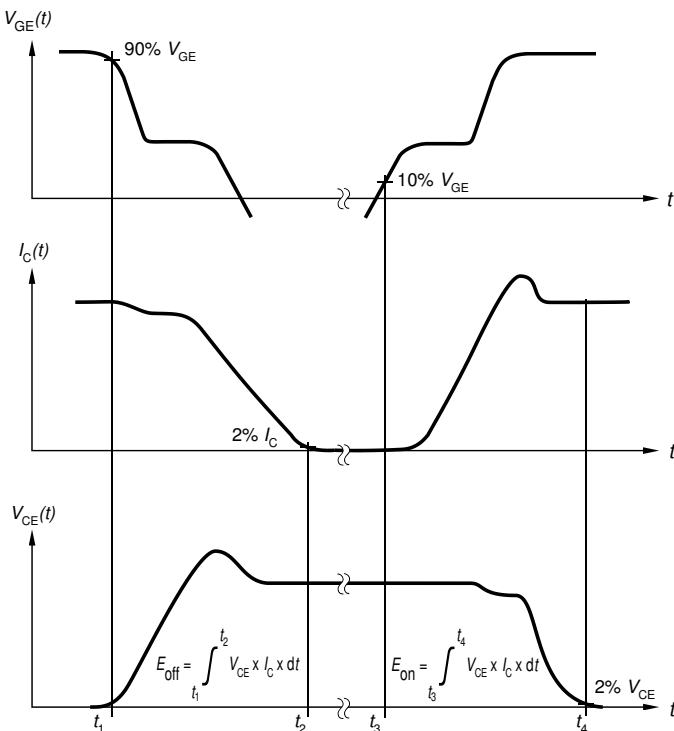


Figure B. Definition of switching losses

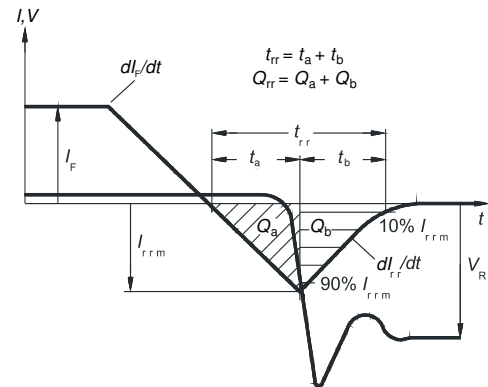


Figure C. Definition of diode switching characteristics

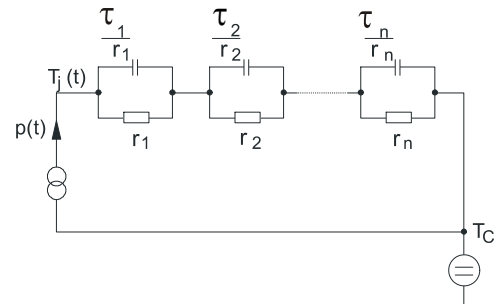


Figure D. Thermal equivalent circuit



Figure E. **Dynamic test circuit**
 Parasitic inductance L_σ ,
 parasitic capacitor C_σ ,
 relief capacitor C_r ,
 (only for ZVT switching)

TRENCHSTOP™ Series**Revision History**

AIKP20N60CT**Revision: 2017-02-09, Rev. 2.1**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2017-02-09	Data sheet created

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